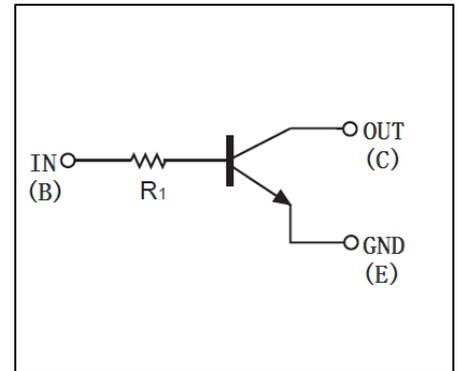


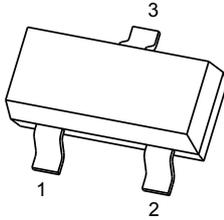
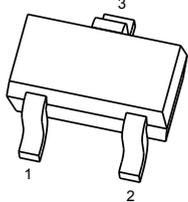
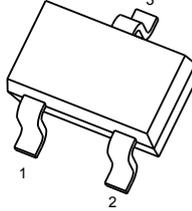
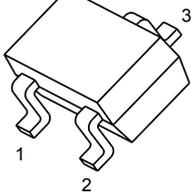
**DTC144TE/DTC144TUA  
DTC144TKA /DTC144TCK**

DIGITAL TRANSISTOR (NPN)

**FEATURES**

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors(see equivalent circuit)
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input.They also have the advantage of almost completely eliminating parasitic effects
- Only the on/off conditions need to be set for operation, making device design easy

**• Equivalent Circuit**

**MARKING:06**
**PIN CONNENCTIONS and MARKING**

<b>DTC144TCK</b>  <b>SOT-23</b> 1. IN 2. GND 3. OUT	<b>DTC144TE</b>  <b>SOT-523</b> 1. IN 2. GND 3. OUT
<b>DTC144TUA</b>  <b>SOT-323</b> 1. IN 2. GND 3. OUT	<b>DTC144TKA</b>  <b>SOT-23-3L</b> 1. IN 2. GND 3. OUT

**MAXIMUM RATINGS(Ta=25°C unless otherwise noted)**

Symbol	Parameter	Limits(DTC144T□)				Unit
		E	UA	KA	CA	
V <sub>CBO</sub>	Collector-Base Voltage	50				V
V <sub>CEO</sub>	Collector-Emitter Voltage	50				V
V <sub>EBO</sub>	Emitter-Base Voltage	5				V
I <sub>C</sub>	Collector Current -Continuous	100				mA
P <sub>D</sub>	Power Dissipation	150	200	200	200	mW
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150				°C

**ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)**

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =50μA, I <sub>E</sub> =0	50			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	50			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =50μA, I <sub>C</sub> =0	5			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =50V, I <sub>E</sub> =0			0.5	μA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			0.5	μA
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =5mA, I <sub>B</sub> =0.5mA			0.3	V
DC current gain	h <sub>FE</sub>	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	100			
Input resistor	R <sub>1</sub>		32.9	47	61.1	kΩ
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>E</sub> =-5mA, f=100MHz		250		MHz

## Typical Characteristics

**Static Characteristic**
